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IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF

MICHIHARU MATSUI ET AL

: EXAMINER: TRAN, T. F.

SERIAL NO: 09/956,986

:

FILED: SEPTEMBER 21, 2001

: GROUP ART UNIT: 2811

FOR: NONVOLATILE
SEMICONDUCTOR MEMORY
DEVICE HAVING ELEMENT
ISOLATING REGION OF TRENCH
TYPE AND METHOD OF
MANUFACTURING THE SAME

AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

In response to the Official Action mailed December 3, 2002, please amend this application as follows:

IN THE CLAIMS

Please amend Claims 1, 3, 5, 32, 34 and 36 to read as follows:¹

A B3

1. A semiconductor device comprising:
a semiconductor layer;
a first insulating film formed on said semiconductor layer;
a first electrode layer formed on said first insulating film;
an element isolating region comprising an element isolating insulating film formed to extend through said first electrode layer and said first insulating film to reach an inner region

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